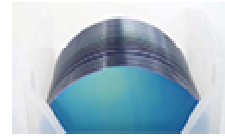




Epitaxial (EPI) Silicon Wafer

Epitaxial (EPI) Silicon Wafer, adopting chemical vapor deposition growth method (CVD), is widely used in the R&D of discrete devices, Si BiCMOS / Si Bipolar / Si CMOS devices, IGBT, devices, power devices and SOI wafer. 4" 5" and 6" are available.



No.	Items	Standard Specifications		
1	General Characteristics			
1-1	Size	4"	5"	6"
1-2	Diameter mm	100±0.5	125±0.5	150±0.5
1-3	Orientation	(100) or (111)	(100) or (111)	(100) or (111)
2	Epitaxial Layer Characteristics			
2-1	Growth Method	CVD	CVD	CVD
2-2	Conductivity Type	P or P+, N/ or N+	P or P+, N/ or N+	P or P+, N/ or N+
2-3	Thickness μm	2.5-120	2.5-120	2.5-120
2-4	Thickness Uniformity	≤3%	≤3%	≤3%
2-5	Resistivity Ω-cm	0.1-50	0.1-50	0.1-50
2-6	Resistivity Uniformity	≤3%	≤5%	-
2-7	Dislocation cm ⁻²	<10	<10	<10
2-8	Surface Quality	No chip, haze or orange peel remains, etc.		
3	Handle Substrate Characteristics			
3-1	Growth Method	CZ	CZ	CZ
3-2	Conductivity Type	P/N	P/N	P/N
3-3	Thickness μm	525-675	525-675	525-675
3-4	Thickness Uniformity max	3%	3%	3%
3-5	Resistivity Ω-cm	As required	As required	As required
3-6	Resistivity Uniformity	5%	5%	5%
3-7	TTV μm max	10	10	10
3-8	Bow μm max	30	30	30
3-9	Warp μm max	30	30	30
3-10	EPD cm ⁻² max	100	100	100
3-11	Edge Profile	Rounded	Rounded	Rounded
3-12	Surface Quality	No chip, haze or orange peel remains, etc.		
3-13	Back Side Finish	Etched or LTO (5000±500Å)		
3-14	Packing	Cassette inside, carton box outside.		

Single Crystal Silicon Ingot

Single Crystal Silicon Ingot is widely used in fabricating diode, transistor, integrated circuit, discrete component, power device, detector, silicon controlled rectifier, etc. 2" 3" 4" 5" 6" 8" and 9.5" are available.



No.	Items	Standard Specifications	
1	Size	2" 3" 4" 5" 6" 8" 9.5"	
2	Diameter mm	50.8-241.3, or as required	
3	Growth Method	CZ or FZ or FZNTD	
4	Conductivity Type	P/Boron, N/Phosphorus or un-doped	
5	Length mm	≥180 or as required	
6	Orientation	(100), (110), (111)	
7	Resistivity Ω-cm	As required	
8	Carbon Content a/cm ³	≤5E16 or as required	
9	Oxygen Content a/cm ³	≤1E18 or as required	
10	Metal Contamination a/cm ³	<5E10 (Cu, Cr, Fe, Ni); <3E10 (Al, Ca, Na, K, Zn)	
11	Packing	Plastic bag inside, carton box outside.	

✉ E2-1-1011 Global Center, No. 1700
Tianfu Avenue North, Chengdu 610041, China

☎ Tel +28 8518 72 51/52/53

Fax+28 8518 4110